

Achievements of the ATLAS Upgrade Planar Pixel Sensors R&D Project

G. Calderini

(on behalf of the ATLAS Planar Pixel Sensors Collaboration)

Laboratoire de Physique Nucléaire et des Hautes Energies (LPNHE) Paris, France

Dipartimento di Fisica E. Fermi, Università di Pisa, Pisa, Italy

Abstract

This paper reports on recent accomplishments and ongoing work of the ATLAS Planar Pixel Sensors R&D project. Special attention is given in particular to new testbeam results obtained with highly irradiated sensors, developments in the field of slim and active edges and first steps towards prototypes of future pixel modules.

Keywords: Planar Silicon radiation detectors, tracking detectors, fabrication technology

1. Introduction

To extend the physics reach of the LHC, accelerator upgrades are planned which will increase the integrated luminosity to beyond 3000 fb^{-1} and the pile-up per bunch-crossing by a factor 5 to 10. To cope with the increased occupancy and radiation damage, the ATLAS experiment plans to introduce an all-silicon inner tracker with the HL-LHC upgrade. To investigate the suitability of pixel sensors using the proven planar technology for the upgraded tracker, the ATLAS Upgrade Planar Pixel Sensor R&D Project (PPS) was established comprising 19 institutes and more than 80 scientists. Main areas of research are the performance assessment of planar pixel sensors with different designs and substrate thicknesses up to the HL-LHC fluence, the achievement of slim or active edges to provide low geometric inefficiencies without the need for shingling of modules and the exploration of possibilities for cost reduction to enable the instrumentation of large areas. This paper gives an overview of recent accomplishments and ongoing work of the R&D project.

2. The planar pixels sensor technology

Planar pixel sensors are widely used since many years in the tracking detectors of many high-energy experiments. This is now a mature and sound technology, allowing to reach a very high production yield at a limited cost. The experience achieved in the construction and in the many years of operations of detectors equipped with planar pixel sensors represent a guarantee for future trackers. At the same time, a few axes of development can be followed to achieve further improvements. Radiation hardness has been increased, currently allowing good operation conditions even after a fluence of a few $10^{15} n_{eq}/\text{cm}^2$ which is what is expected for the non-innermost pixel layers during the Phase-II of the LHC upgrade. Special processes are under study to allow an increased geometrical efficiency by reducing the size of the dead region at the edge of the sensors.

This is critical in the assembly of the staves, where the modules are tiled, or for layers in which there is not enough room to stagger the staves in the $r - \phi$ plane to allow an overlap of the corresponding active regions. A few options, as larger wafers, multi-sensor modules or processes as the n-in-p, are also being developed to further reduce the cost of the productions.

3. Development of active-edge sensors

The need to reduce as much as possible the size of the dead region at the border of the sensors has driven the planar pixel community to use intensely the device simulation tools available and optimise the sensor layout. Good results have been achieved by reducing the guard ring region, which represents a low-efficiency portion of the sensor due to the lower electrical field and the distance from the first row of pixels. Already for the design of the ATLAS Insertable B-Layer sensors, preliminary simulations (see for instance [1]) had indicated that the number of guard rings could be reduced and the n-in-n nature of the sensors, in which pixels and guard rings are on opposite faces, could allow to push the first row of pixels inside the guard-ring area. Beam-test analysis showed that some charge collection efficiency was still possible for particles crossing the detector in this region (Fig. 1), thus allowing an improvement of the geometrical acceptance. The solution has been indeed adopted for the ATLAS IBL sensors.

More recently, further optimisation in the number of the guard-rings has been achieved in both n-in-n and n-in-p productions, allowing to reduce the size of the inefficient region down to a typical scale of $300 - 400 \mu\text{m}$ (see for example [2]). In addition, an alternative approach based on the use of DRIE (Deep Reactive Ion Etching) and SCP (Scribe, Cleave, Passivate) techniques has allowed the construction of active-edge devices. In the first case the method consists in producing sensors with an edge doping of the same type with respect to the back-side. The net result is to have the cut-line inside an equipotential region, where the absence of electrical field prevents the generation of

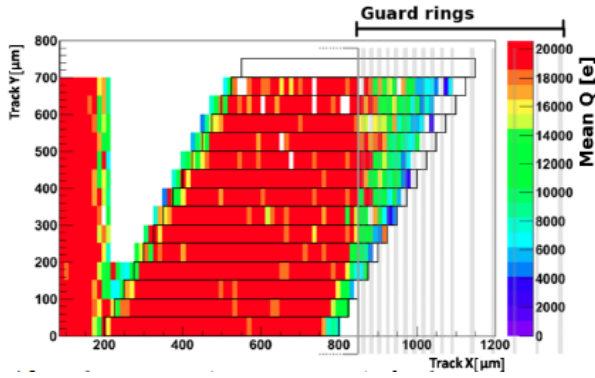


Figure 1: Beam-test analysis of special sensors developed to study the layout optimisation for the ATLAS IBL. Each horizontal rectangle represents a block of pixels and each block is pushed at different positions below the guard rings, which are implanted on the opposite face.

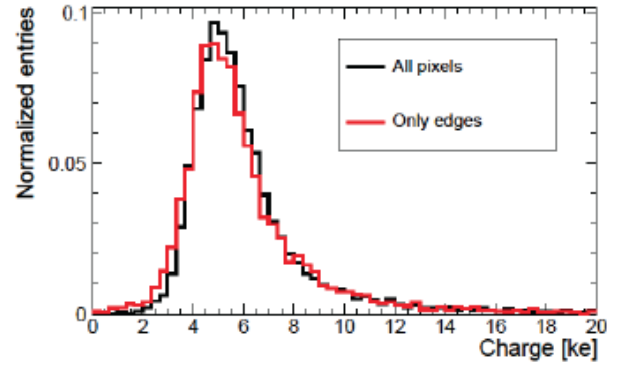


Figure 3: Beam test analysis of collected charge for VTT active-edge sensors. The inclusive distribution and the one for the pixels of the first row are very similar.

69 edge surface current. Different processes allow this result. A
 70 production of n-in-p devices at VTT [3, 4] uses DRIE to exca-
 71 cavate a deep and large trench in order to expose the side. A
 72 lateral implantation is then started so that the doping of the ver-
 73 tical region becomes similar to that of the backside (see Fig.
 74 2).

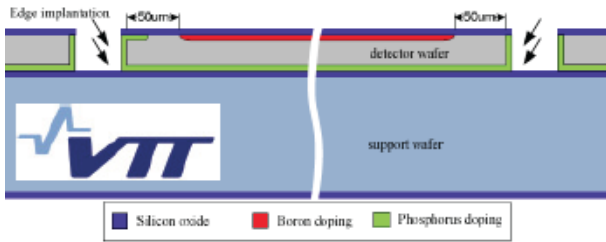


Figure 2: Sketch of the VTT process to achieve active-edge sensors

75 Using this technique, 100 μm and 200 μm -thick n-in-p sen-
 76 sors are produced in collaboration with MPP Munich, with a
 77 distance of the first pixel from the edge of the order of 50 and
 78 125 μm . Beam test results indicate that the collected charge dis-
 79 tribution is identical for the pixels of the first row and the others,
 80 thus showing that the concept works (see Fig. 3).

81 The beam-test analysis indicates that a hit efficiency of
 82 $84^{+9}_{-14}\%$ is achieved in the last 50 μm of the sensor edge, be-
 83 yond the last pixel implant.

84 A similar method is used in the FBK (Fondazione Bruno
 85 Kessler) [5] process. In this case, the deep trench is again exca-
 86 vated by DRIE, but the lateral doping is obtained by diffusion
 87 instead of implantation. The doped trench is finally filled with
 88 poly-silicon [6, 7]. The uniformity of the poly-silicon filling is
 89 a critical phase of the process. Residuals of air in the 200 μm -
 90 deep and 4.5 μm -wide trench (Fig. 4) could severely damage
 91 the device during the high-temperature phases of the process.

92 Using this technique, 200 μm thick n-in-p sensors are pro-
 93 duced by FBK in collaboration with LPNHE Paris. ATLAS
 94 FE-I3 and FE-I4 designs [8] are used, with different guard-ring
 95 numbers and edge distance configurations. The distance of the

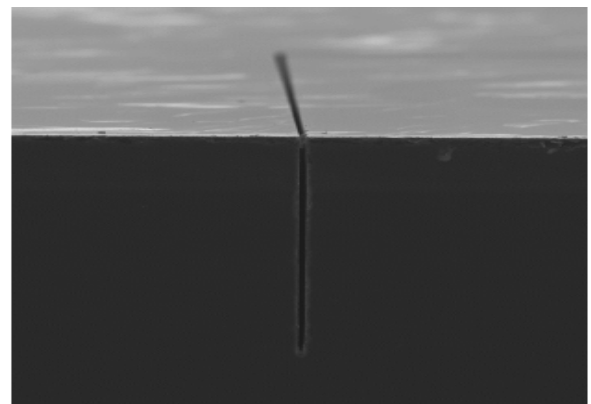


Figure 4: Detail of a deep trench produced by DRIE on a test bulk at FBK

96 first row of pixels from the cut-line is typically of the order of
 97 100 – 200 μm (Fig. 5).

98 Baby-detectors with a reduced number of pixels but the same
 guard-ring and edge configuration as the main structures are
 also produced on the same wafers for test purpose. Measure-
 ments show a breakdown voltage exceeding the 100V (even
 200V for sensors with more than 1 guard ring), in excellent
 agreement with simulations (see Fig. 6).

Simulations indicate that even at a dose of $10^{15} n_{eq}/\text{cm}^2$ the
 charge collection efficiency of the pixels of the first row is still
 significant with respect to the pixels of the central region, pro-
 vided that a bias voltage exceeding 2-300V is applied (see Fig.
 7).

The sensors are presently being bump-bonded to ATLAS FE-
 I4 chips to be analysed at beam-tests.

A different approach to the problem of edge current has been
 tested by SCIPP (UCSC) [9] in collaboration with U.S. Naval
 Research Lab (NRL) [10]. A Scribe-Cleave-Passivate (SCP)
 technique has been used to block the edge current in the sensors
 [11, 12]. In this approach the detector is scribed along the edge
 by laser or XeF_2 etching and cleaved. Once the edge is exposed,
 the sensor undergoes a passivation phase via plasma-enhanced
 CVD or alumina deposition (see Fig. 8).

The fixed interface charge determined by the passivation pro-

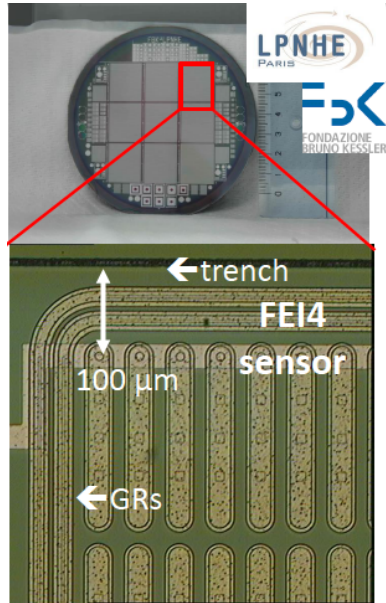


Figure 5: Detail of the edge region of a 2-guard-ring FE-14 geometry pixel sensor.

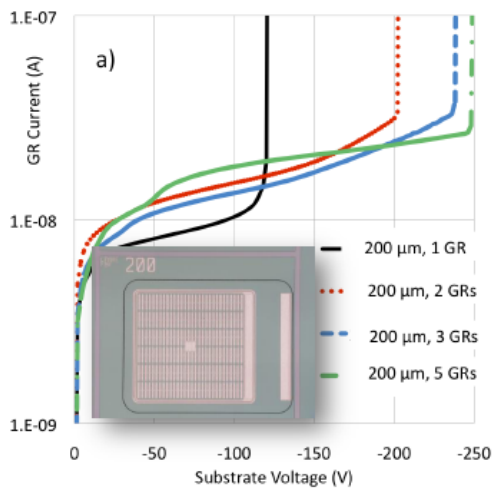


Figure 6: Typical IV behaviour of IV curves for baby detectors with 1, 2, 3, and 5 guard rings. The curves are in very good qualitative agreement with simulations.

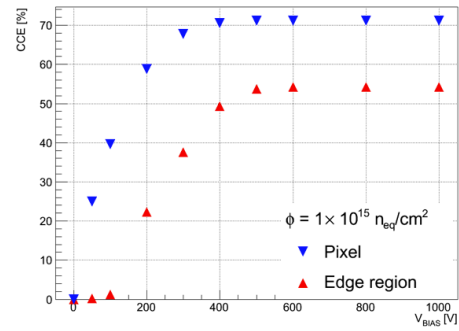


Figure 7: Expected charge collection efficiency after a $10^{15} n_{eq}/cm^2$ dose as a function of bias voltage for central and edge pixels (simulation) .

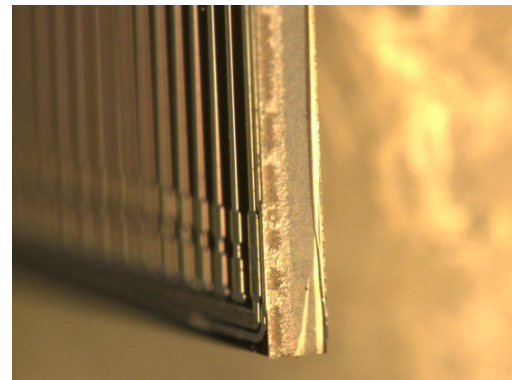


Figure 8: Photo of the sensor sidewall after cleaving and passivation phase.

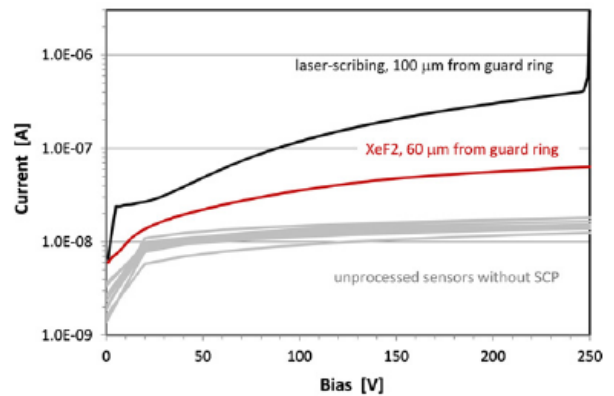


Figure 9: Leakage current behaviour for sensors scribed with a laser (more damaging) at a distance of $100\mu m$ from the guard ring and with XeF_2 PECVD (less damaging) at a distance of $60\mu m$. In the second case, in spite of the reduced distance, the current is lower due to the better quality of the scribing

cess allows to control the potential across the sidewall, minimising the edge current (see Fig. 9) [13].

Further investigations are under way to determine the behaviour of the sensors treated with SCP after radiation damage.

4. Reducing the costs

One of the key activities in the recent development of planar pixel sensors has been the attempt to reduce the cost of productions. This is critical whenever the use of planar pixels is targeted for middle- and large-surface detectors, as is the case for the external layers of a tracker. Several axes of research have been developed.

4.1. Cheaper interconnections

Significant R&D has been devoted to reduce the price of sensor-FEE interconnections per unit area, by replacing the standard bump-bonding by cheaper technologies. In the framework of the ATLAS PPS project, MPP Munich in collaboration with Fraunhofer EMFT [14] has investigated the possible use of Solid-Liquid Inter-Diffusion (SLID) process [4]. The smaller number of process steps with respect to bump-bonding could

139 translate in reduced cost. In addition, the limitations on the
 140 geometrical pitch are less severe in this technology. Wafer to
 141 wafer as well as chip to wafer connections are feasible. SLID-
 142 based modules are expected to be delivered by the end of 2013
 143 and they will be characterised with beam-tests.

144 Alternative low-cost bonding technologies as the IBM C4NP
 145 [15] are also being evaluated by the ATLAS PPS Collaboration.

146 4.2. Multi-chip modules

147 An effective solution to achieve lower-cost productions is the
 148 development of larger sensors, which is made possible by the
 149 use of larger wafers by foundries, and the assembly of multi-
 150 chip modules. Many sensor providers recently moved their pro-
 151 ductions to 6-inch and even 8-inch wafers. This allows the opti-
 152 misation of the wafer layout and the presence of more large-area
 153 sensors on the same wafer, features which translate globally
 154 into a significant cost-reduction. On the other hand, the larger
 155 size of the sensors allows the assembly of multi-chip modules,
 156 with a consequent reduction of the number of handling opera-
 157 tions per unit of area and a significant cost reduction. These
 158 larger sensors can fit well the specifications for outer layers and
 159 the side end-cap regions. In the framework of the ATLAS PPS
 160 Collaboration, recent productions of large "quad" sensors on 6-
 161 inch wafers have been done at CiS [16], HPK (see Fig. 10) [17]
 and Micron (see Fig. 11) [18]. Some of the multi-chip mod-

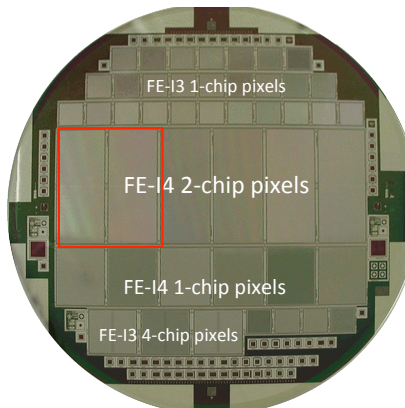


Figure 10: Layout of a recent 6-inch production by Hamamatsu Photonics KK, in collaboration with the ATLAS Japan Silicon group. The large 2x2 FE-I4-design sensors are visible in the central part of the wafer, together with FE-I4-design and FE-I3-design single sensors.

162 ules have already been measured at beam-tests and the analysis
 163 of the results is underway.

165 5. Design improvements

166 In addition to the cost reduction, an important line of re-
 167 search consists in the further optimisation of the sensor design
 168 to achieve the best possible performance even after heavy irra-
 169 diation and years of operation in a high-energy physics experi-
 170 ment. One of the critical issues with the punch-through struc-
 171 ture of the biasing system is a certain loss of efficiency in the
 172 dot region after irradiation. An effort has been made to provide
 173 different biasing schemes in order to avoid such a problem. The

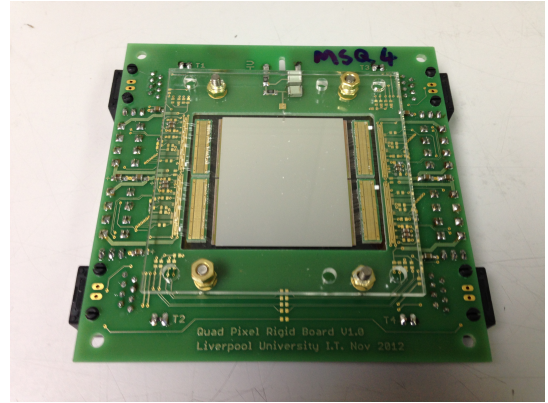


Figure 11: Detail of a large 2x2 sensor produced by Micron in collaboration with the ATLAS Liverpool and Glasgow groups. The sensors is already bump-bonded and mounted on the periphery card to be read-out and installed in the beam-test.

design of bias paths with poly-silicon structures has been stud-
 174 ied by the ATLAS Japan Silicon group, which has proposed a
 175 number of solutions over the years. The position of the poly-
 176 silicon line inside the pixel is of great importance since it can
 177 affect the charge collection efficiency. A new design has been
 178 recently proposed in which the line runs along the inner part of
 179 the pixel edge, which seems to optimise the hit efficiency, even
 180 after radiation damage. In addition a new proposal of biasing
 181 scheme for $25 \times 500 \mu\text{m}$ pixels has been proposed. In this design
 182 the bias lines are staggered on alternating pixels (see Fig. 12).
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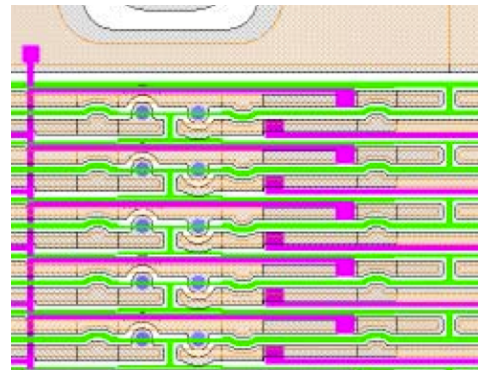


Figure 12: Detail of the poly-silicon biasing scheme for a sensor with $25 \times 500 \mu\text{m}$ pixels designed by the ATLAS Japan Silicon group and produced by Hamamatsu Photonics KK. The biasing lines are staggered on neighboring pixels.

A different technique has been proposed by the ATLAS
 group of Dortmund, which studied a distribution scheme ob-
 tained by bias rails, narrow metal strips running over the oxide
 layer and providing the electrical network to the pixels. Also
 in this case the geometrical configuration can influence the hit
 efficiency and several different concepts have been tested (see
 Fig. 13).

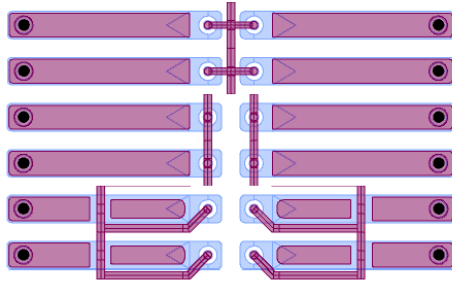


Figure 13: Detail of the metal biasing scheme for a sensor with $50 \times 250 \mu\text{m}$ pixels designed by the ATLAS Dortmund group and produced by CiS. Different geometry designs have been tested to optimise the sensor performance.

6. Bulk materials

Special mention needs to be done for a recent study by the ATLAS Dortmund group, which is trying to improve the radiation hardness of n-in-n sensors by the use of a MCz bulk. The intermediate layers of the upgraded ATLAS tracker will be exposed to a mix of ionising and non-ionising radiation. MCz material is expected to have a better performance with respect to standard DOFZ bulk under these conditions [19]. For this reason, MCz FE-I4-design prototype sensors have been produced and irradiated with protons at the CERN PS up to three different fluences ($0.8, 1.6$ and $3.0 \cdot 10^{15} n_{eq}/\text{cm}^2$). After this first phase they have been tested with a ^{90}Sr source and at a beam-test at CERN, showing a good residual charge collection efficiency, at least for the first two irradiation samples.

They are presently undergoing the second phase of irradiation, the one involving neutrons, at the Ljubljana reactor. The plan is to test them again in one of the next PPS beam-test.

7. Conclusions

Planar pixel sensors represent a sound and well-established technology for the tracking detectors of high-energy physics experiments. Many activities are developed in parallel in the framework of the ATLAS PPS Collaboration to improve the sensors performance, even after the heavy irradiations expected in the Phase-II of LHC, and to reduce the costs of productions. New developments in techniques of fabrication of active-edge sensors have been presented. Progress in interconnection technology allows to reduce the cost of module productions, as well as the use of larger sensors and multi-chip modules. New solutions for the biasing schemes have been presented.

8. Acknowledgements

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